



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

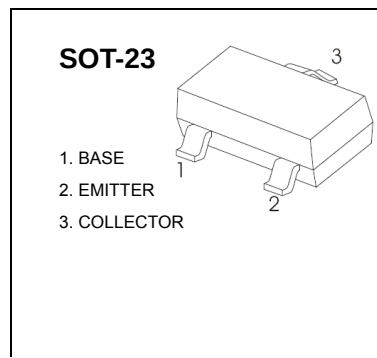
S9014 TRANSISTOR (NPN)

FEATURES

- Complementary to S9015

MARKING: J6

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)



Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.2	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}$, $I_B = 0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{V}$, $I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 35\text{V}$, $I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3\text{V}$, $I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}$, $I_B = 5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100\text{mA}$, $I_B = 5\text{mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$ $f = 30\text{MHz}$	150			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-450	450-1000

Typical Characteristics

S9014

